IN THE CLAIMS:

Please **AMEND** the claims as follows:

1. (Currently Amended) A nitride based semiconductor laser device comprising:

a transparent substrate having conductive properties;

a nitride based semiconductor layer formed on one surface of said transparent substrate and constituting a cavity having a front facet on a side of laser light emission and a rear facet on an opposite side from said front facet;

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a first ohmic electrode of a first conduction type formed on the other surface of said transparent substrate; and

a second ohmic electrode of a second conduction type formed on said nitride based semiconductor layer,

wherein at least one of said first and second ohmic electrodes ~~being~~ is formed in such a shape or arrangement that the ~~forward and backward directions along the cavity length~~ directions of the front facet and the rear facet of said cavity of said nitride based semiconductor layer can be distinguished.

2. (Original) The nitride based semiconductor laser device according to claim 1, wherein said first ohmic electrode and said second ohmic electrode have different shapes.

3. (Original) The nitride based semiconductor laser device according to claim 1, wherein said first ohmic electrode and said second ohmic electrode have the same shape.

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4. (Original) The nitride based semiconductor laser device according to claim 1, wherein said second ohmic electrode is arranged on a region different from a region above a region where said first ohmic electrode is formed in said nitride based semiconductor layer.

5. (Original) The nitride based semiconductor laser device according to claim 1, wherein said transparent substrate is composed of gallium nitride or silicon carbide.

6. (Original) The nitride based semiconductor laser device according to claim 1, wherein said nitride based semiconductor layer contains at least one of gallium, aluminum, indium, boron, and thallium.

7. (Original) The nitride based semiconductor laser device according to claim 1, wherein at least one of said first and second ohmic electrodes is asymmetric with respect to a line passing through a center point of said cavity length and vertical to the cavity length direction.

8. (Original) The nitride based semiconductor laser device according to claim 1, wherein said nitride based semiconductor layer has a striped current injection region, and

said first and second ohmic electrodes respectively have regions opposite to said striped current injection region.

9. (Original) The nitride based semiconductor laser device according to claim 1, further comprising

dielectric films respectively formed at a front facet and a rear facet of said cavity.

10. (Original) The nitride based semiconductor laser device according to claim 9, wherein said dielectric films respectively formed at the front facet and the rear facet of said cavity have different reflectances.

11. (Original) The nitride based semiconductor laser device according to claim 1, wherein said nitride based semiconductor layer comprises a cladding layer of a first conduction type, an active layer, and a cladding layer of a second conduction type.

12-21. (Withdrawn)